INA181 双向低侧和高侧电压输出电流感应放大器

1 特性

- 共模范围 (V_{CM})：–0.2V 至 +26V
- 高带宽：350kHz
- 偏移电压：
  - ±150μV（最大值），V_{CM} = 0V
  - ±500μV（最大值），V_{CM} = 12V
- 输出转换率：2V/μs
- 双向电流感应功能
- 精度：
  - ±1% 增益误差（最大值）
  - 1-μV/°C 偏移漂移（最大值）
- 增益选项：
  - 20 V/V（A1 器件）
  - 50 V/V（A2 器件）
  - 100 V/V（A3 器件）
  - 200 V/V（A4 器件）
- 静态电流：260μA（每个通道的最大值）

2 应用

- 电机控制
- 电池监控
- 电源管理
- 照明控制
- 过流检测

3 说明

INA181 是一系列经成本优化的双向电流感应放大器（也称为电流分流监控器），可在独立于电源电压的 –0.2V 至 +26V 共模电压感测电流感应电阻器上的压降。INA181 以四个固定增益器件选项集成匹配电阻器增益网络：20 V/V、50 V/V、100 V/V 或 200 V/V。该匹配增益电阻器网络可最大限度地减小增益误差并降低温度漂移。

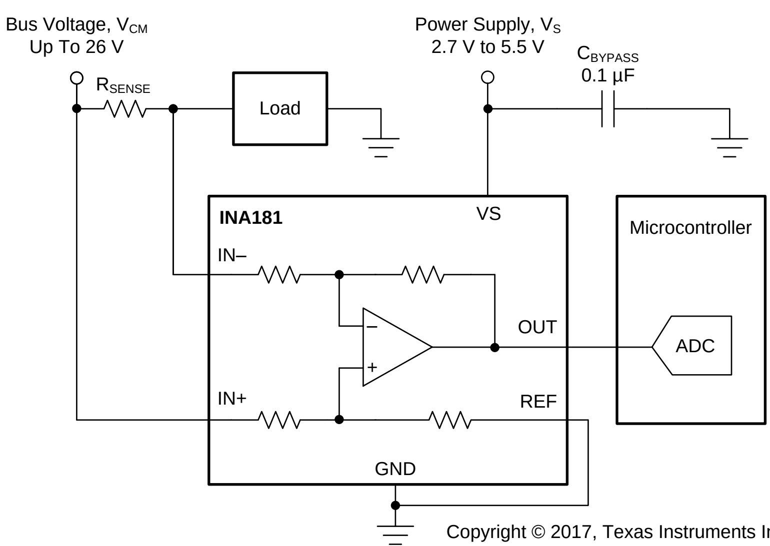
INA181 由一个 2.7V 至 5.5V 的单电源供电，消耗 260μA 的最大电源电流。

所有器件选项均具有扩展级额定工作温度范围（-40°C 至 +125°C），并且采用 6 引脚 SOT-23 封装。

器件信息(1)

器件型号	封装	封装尺寸（标称值）
INA181	SOT-23 (6)	2.90mm x 1.60mm

(1) 要了解所有可用封装，请见数据表末尾的封装选项附录。



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4 修订历史记录

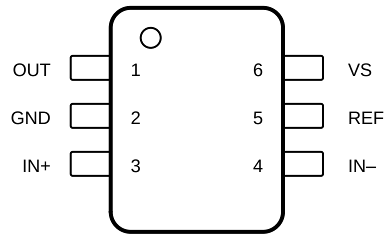
日期	修订版本	注释
4 月	*	首次发布。

5 Device Comparison Table

PRODUCT	CHANNEL	GAIN (V/V)
INA181A1	1	20
INA181A2	1	50
INA181A3	1	100
INA181A4	1	200

6 Pin Configurations and Functions

DBV Package
6-Pin SOT-23
Top View



Not to scale

Pin Functions

PIN		TYPE	DESCRIPTION
NAME	NO.		
GND	2	Analog	Ground
IN–	4	Analog input	Current-sense amplifier negative input. For high-side applications, connect to load side of sense resistor. For low-side applications, connect to ground side of sense resistor.
IN+	3	Analog input	Current-sense amplifier positive input. For high-side applications, connect to bus-voltage side of sense resistor. For low-side applications, connect to load side of sense resistor.
OUT	1	Analog output	Output voltage
REF	5	Analog input	Reference input
VS	6	Analog	Power supply, 2.7 V to 5.5 V

7 Specifications

7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

		MIN	MAX	UNIT
Supply voltage, V_S			6	V
Analog inputs, IN+, IN–(2)	Differential (V_{IN+}) – ($V_{IN–}$)	–26	26	V
	Common-mode(3)	GND – 0.3	26	
Input voltage range	at REF pin	GND – 0.3	V_S + 0.3	V
Output voltage		GND – 0.3	V_S + 0.3	V
Maximum output current, I_{OUT}			8	mA
Operating free-air temperature, T_A		–55	150	°C
Junction temperature, T_J			150	°C
Storage temperature, T_{stg}		–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) V_{IN+} and $V_{IN–}$ are the voltages at the IN+ and IN– pins, respectively.
(3) Input voltage at any pin can exceed the voltage shown if the current at that pin is limited to 5 mA.

7.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	±3000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101(2)	±1000	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

7.3 Recommended Operating Conditions

		MIN	NOM	MAX	UNIT
V_{CM}	Common-mode input voltage (IN+ and IN–)	–0.2	12	26	V
V_S	Operating supply voltage	2.7	5	5.5	V
T_A	Operating free-air temperature	–40		125	°C

7.4 Thermal Information

THERMAL METRIC (1)		INA181 DBV (SOT-23) 6 PINS	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance	198.7	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	120.9	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	52.3	°C/W
ψ_{JT}	Junction-to-top characterization parameter	30.3	°C/W
ψ_{JB}	Junction-to-board characterization parameter	52.0	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.

7.5 Electrical Characteristics

at T_A = 25°C, V_S = 5 V, V_{REF} = V_S / 2, V_{IN+} = 12 V, and V_{SENSE} = V_{IN+} – $V_{IN–}$ (unless otherwise noted)

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNIT
INPUT						
CMRR	Common-mode rejection ratio, RTI (1)	V_{IN+} = 0 V to 26 V, V_{SENSE} = 0 mV, T_A = –40°C to +125°C	84	100		dB
V_{OS}	Offset voltage, RTI	V_{SENSE} = 0 mV		±100	±500	µV
		V_{SENSE} = 0 mV, V_{IN+} = 0 V		±25	±150	µV
dV_{OS}/dT	Offset drift, RTI	V_{SENSE} = 0 mV, T_A = –40°C to +125°C		0.2	1	µV/°C
PSRR	Power-supply rejection ratio, RTI	V_S = 2.7 V to 5.5 V, V_{IN+} = 12 V, V_{SENSE} = 0 mV		±8	±40	µV/V
I_{IB}	Input bias current	V_{SENSE} = 0 mV, V_{IN+} = 0 V		-6		µA
		V_{SENSE} = 0 mV		75		µA
I_{IO}	Input offset current	V_{SENSE} = 0 mV		±0.05		µA
OUTPUT						
G	Gain	A1 devices		20		V/V
		A2 devices		50		V/V
		A3 devices		100		V/V
		A4 devices		200		V/V
E_G	Gain error	V_{OUT} = 0.5 V to V_S – 0.5 V, T_A = –40°C to +125°C		±0.1%	±1%	
	Gain error vs temperature	T_A = –40°C to +125°C		1.5	20	ppm/°C
	Nonlinearity error	V_{OUT} = 0.5 V to V_S – 0.5 V		±0.01%		
	Maximum capacitive load	No sustained oscillation		1		nF
VOLTAGE OUTPUT (2)						
V_{SP}	Swing to V_S power-supply rail (3)	R_L = 10 kΩ to GND, T_A = –40°C to +125°C		(V_S) – 0.02	(V_S) – 0.03	V
V_{SN}	Swing to GND (3)	R_L = 10 kΩ to GND, T_A = –40°C to +125°C		(V_{GND}) + 0.0005	(V_{GND}) + 0.005	V
FREQUENCY RESPONSE						
BW	Bandwidth	A1 devices, C_{LOAD} = 10 pF		350		kHz
		A2 devices, C_{LOAD} = 10 pF		210		kHz
		A3 devices, C_{LOAD} = 10 pF		150		kHz
		A4 devices, C_{LOAD} = 10 pF		105		kHz
SR	Slew rate			2		V/µs
NOISE, RTI (1)						
	Voltage noise density			40		nV/√Hz
POWER SUPPLY						
I_Q	Quiescent current	V_{SENSE} = 0 mV		195	260	µA
		V_{SENSE} = 0 mV, T_A = –40°C to +125°C			300	µA

(1) RTI = referred-to-input.
(2) See 图 19.
(3) Swing specifications are tested with an overdriven input condition.

7.6 Typical Characteristics

at T_A = 25°C, V_S = 5 V, V_{REF} = V_S / 2, and V_{IN+} = 12 V (unless otherwise noted)

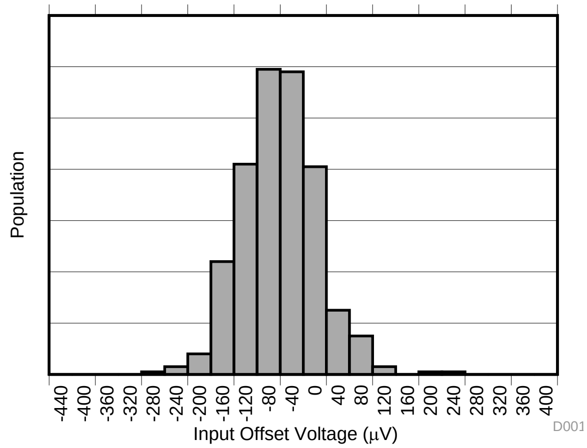


图 1. Input Offset Voltage Production Distribution A1

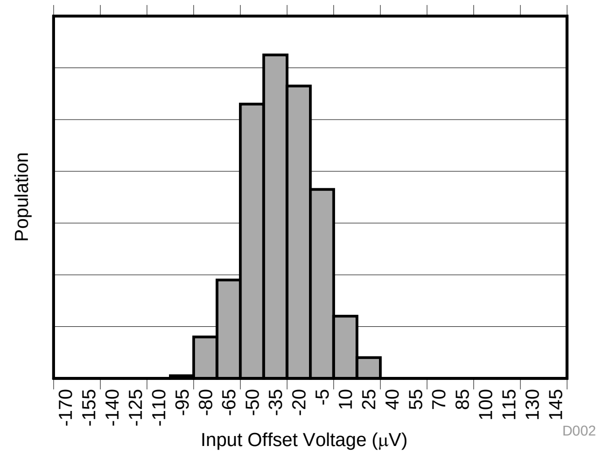


图 2. Input Offset Voltage Production Distribution A2

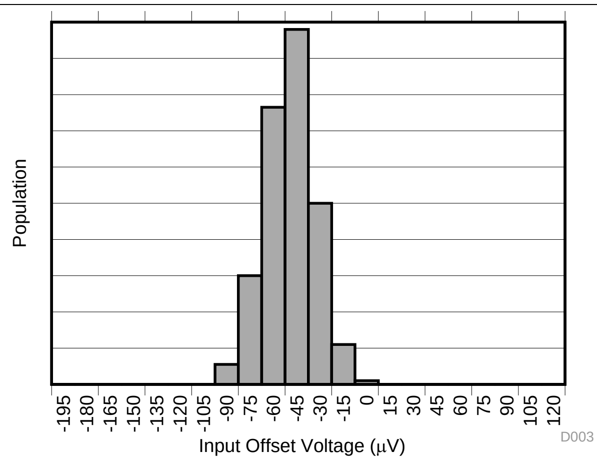


图 3. Input Offset Voltage Production Distribution A3

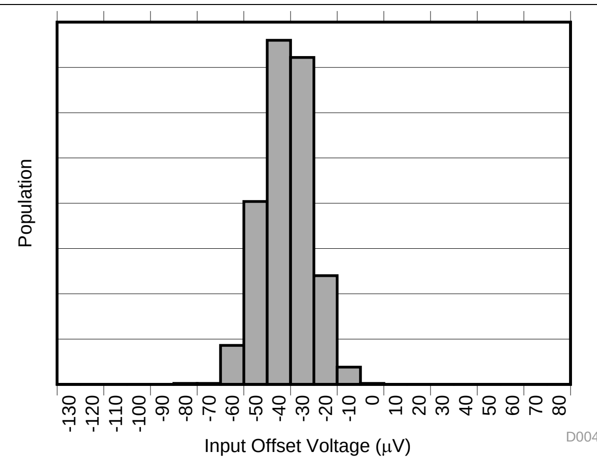


图 4. Input Offset Voltage Production Distribution A4

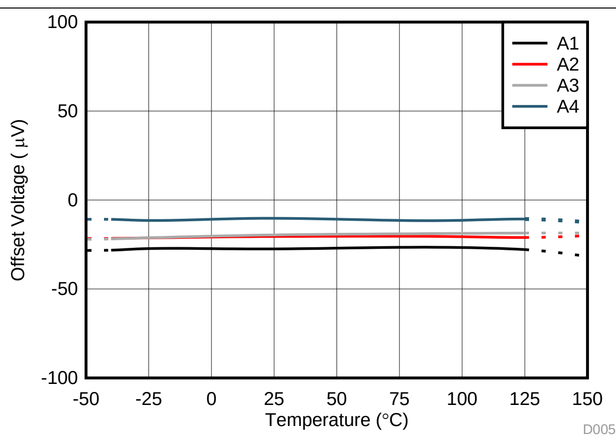


图 5. Offset Voltage vs Temperature

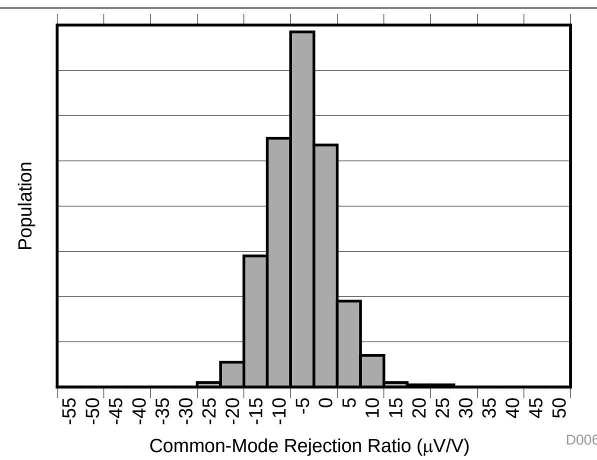


图 6. Common-Mode Rejection Production Distribution A1

Typical Characteristics (接下页)

at T_A = 25°C, V_S = 5 V, V_{REF} = V_S / 2, and V_{IN+} = 12 V (unless otherwise noted)

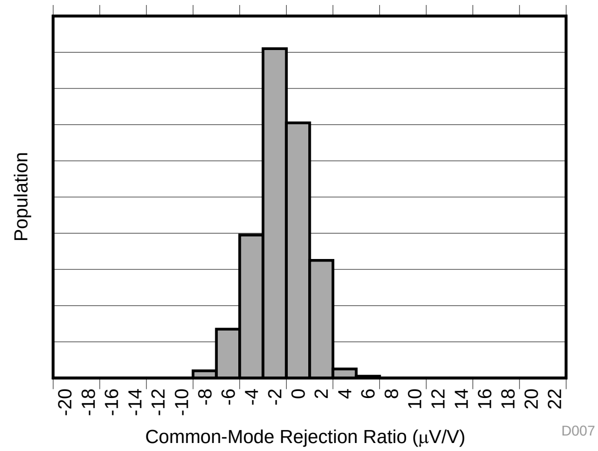


图 7. Common-Mode Rejection Production Distribution A2

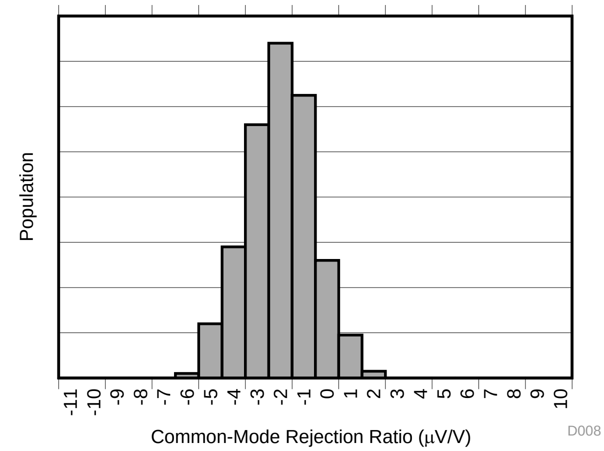


图 8. Common-Mode Rejection Production Distribution A3

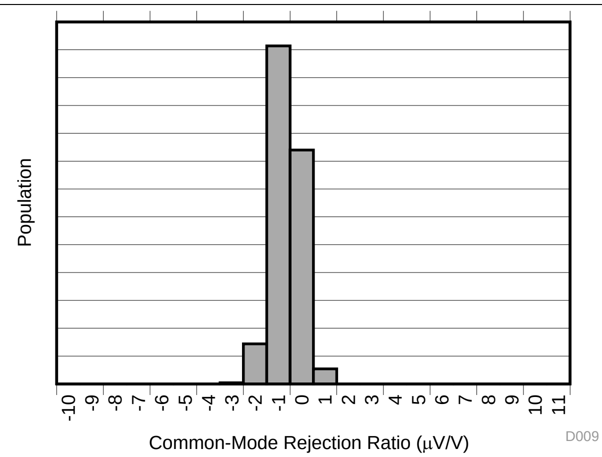


图 9. Common-Mode Rejection Production Distribution A4

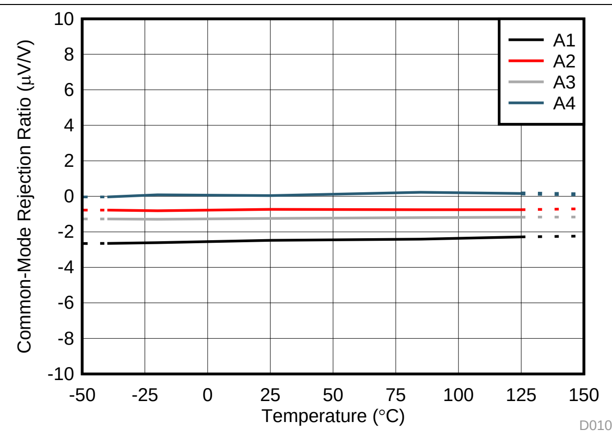


图 10. Common-Mode Rejection Ratio vs Temperature

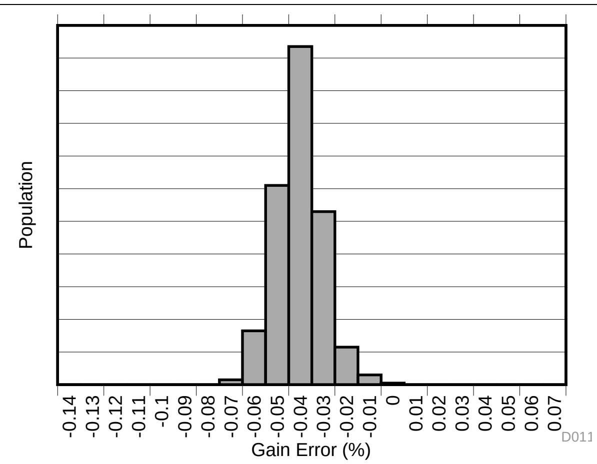


图 11. Gain Error Production Distribution A1

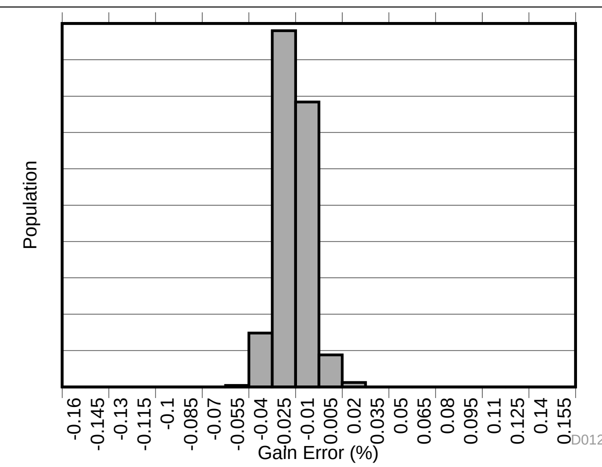


图 12. Gain Error Production Distribution A2

Typical Characteristics (接下页)

at T_A = 25°C, V_S = 5 V, V_{REF} = V_S / 2, and V_{IN+} = 12 V (unless otherwise noted)

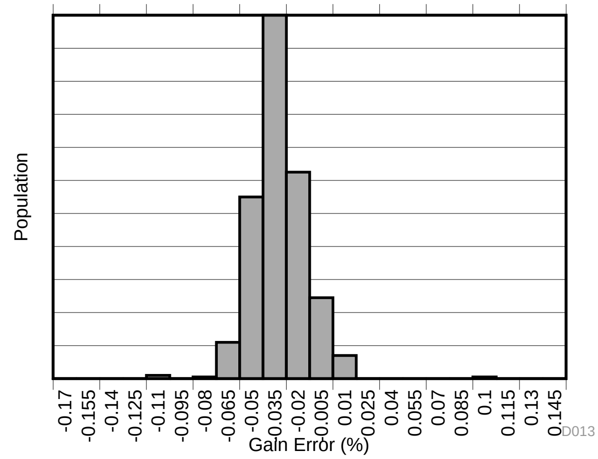


图 13. Gain Error Production Distribution A3

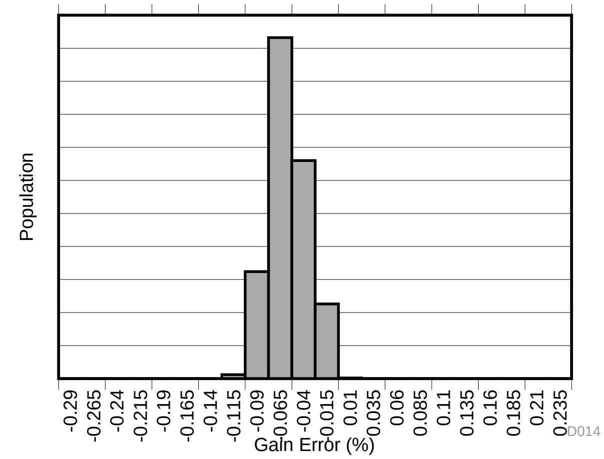


图 14. Gain Error Production Distribution A4

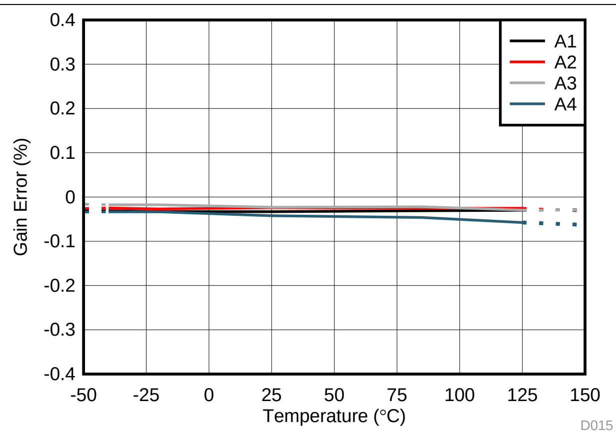


图 15. Gain Error vs Temperature

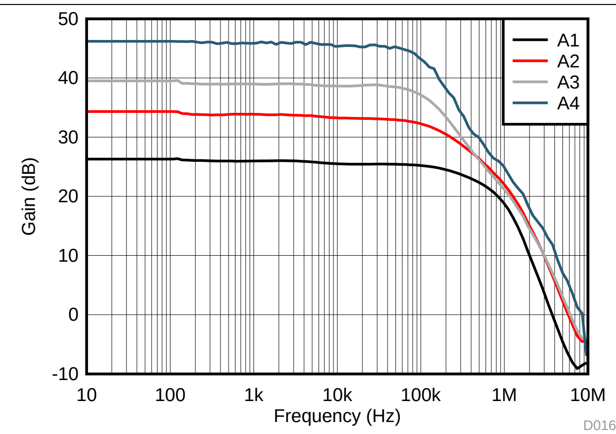


图 16. Gain vs Frequency

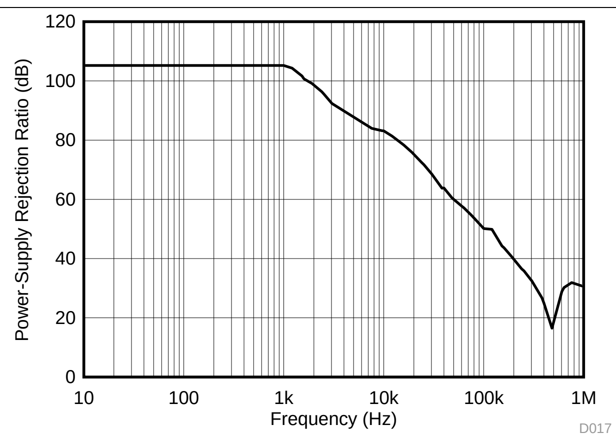


图 17. Power-Supply Rejection Ratio vs Frequency

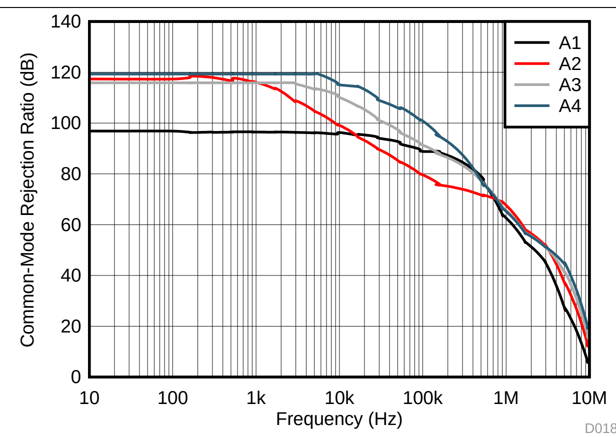


图 18. Common-Mode Rejection Ratio vs Frequency

Typical Characteristics (接下页)

at T_A = 25°C, V_S = 5 V, V_{REF} = V_S / 2, and V_{IN+} = 12 V (unless otherwise noted)

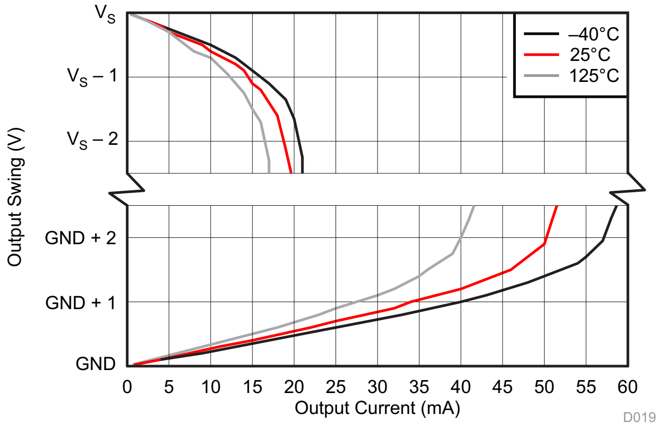


图 19. Output Voltage Swing vs Output Current

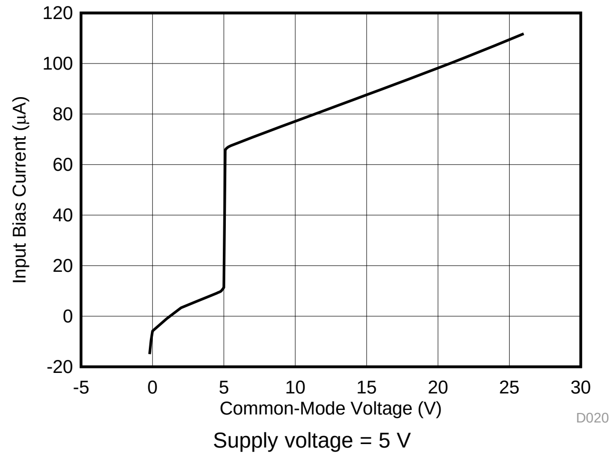


图 20. Input Bias Current vs Common-Mode Voltage

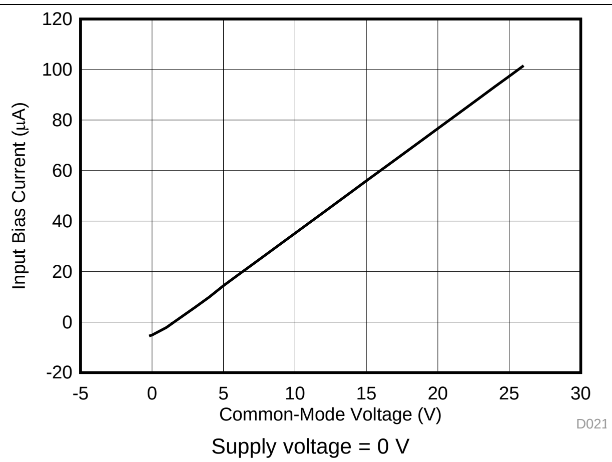


图 21. Input Bias Current vs Common-Mode Voltage (Shutdown)

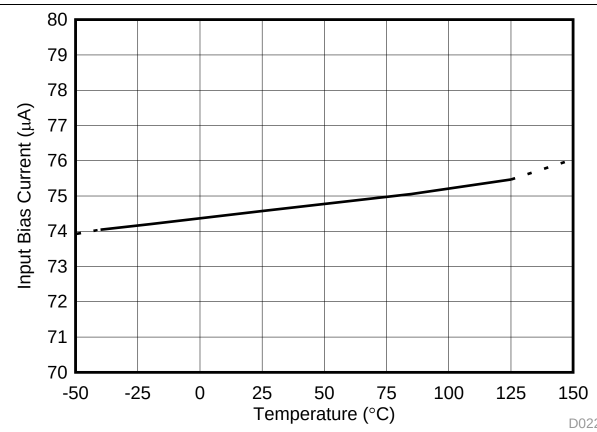


图 22. Input Bias Current vs Temperature

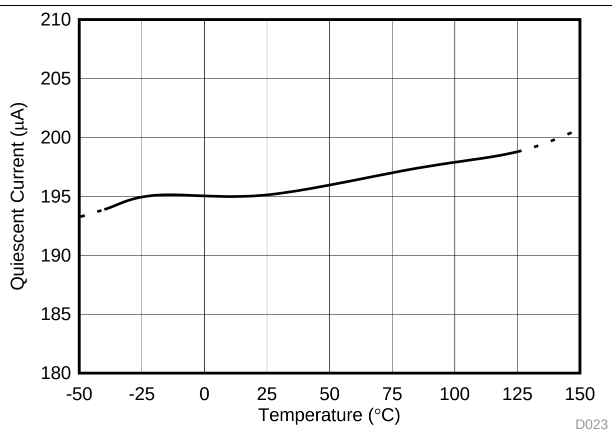


图 23. Quiescent Current vs Temperature

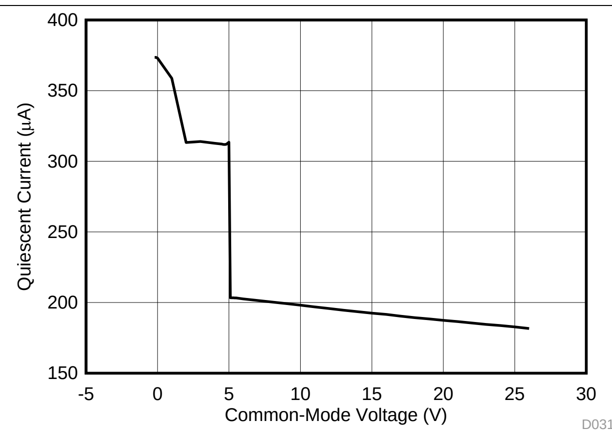


图 24. I_Q vs Common-Mode Voltage

Typical Characteristics (接下页)

at T_A = 25°C, V_S = 5 V, V_{REF} = V_S / 2, and V_{IN+} = 12 V (unless otherwise noted)

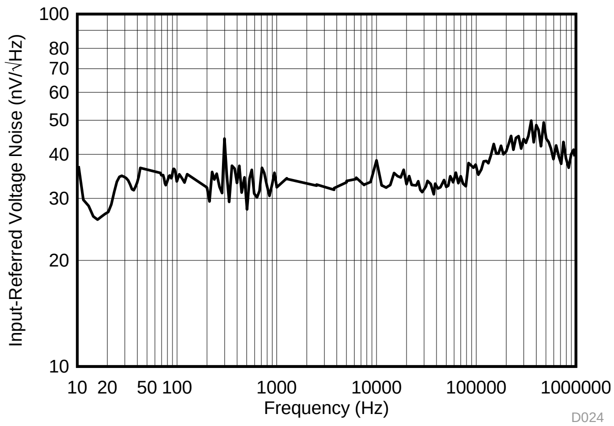


图 25. Input-Referred Voltage Noise vs Frequency

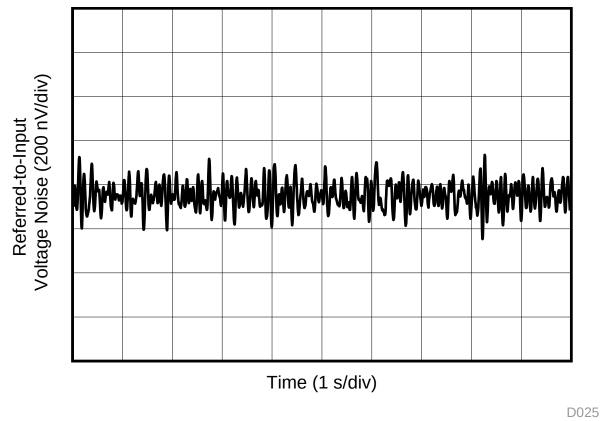
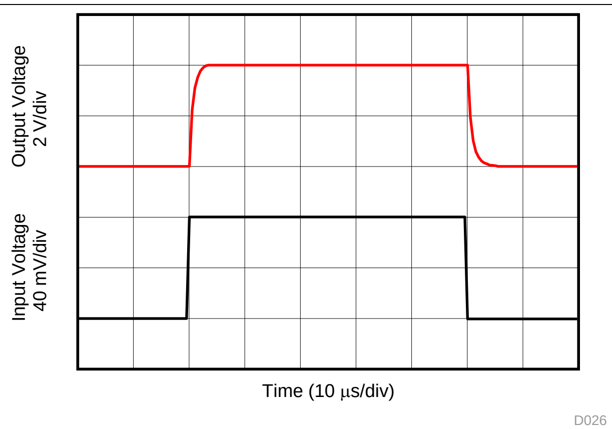


图 26. 0.1-Hz to 10-Hz Voltage Noise (Referred-to-Input)



80-mV$_{PP}$ input step

图 27. Step Response

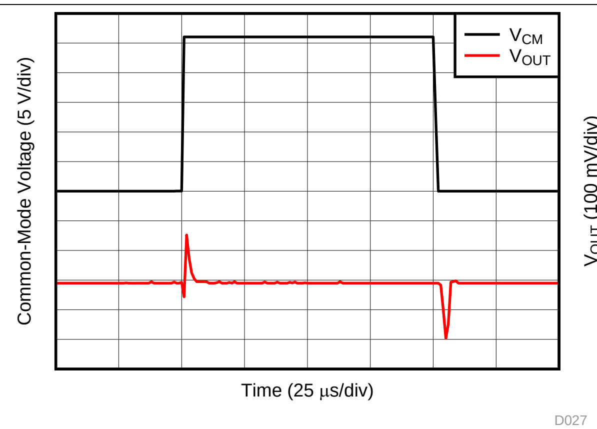


图 28. Common-Mode Voltage Transient Response

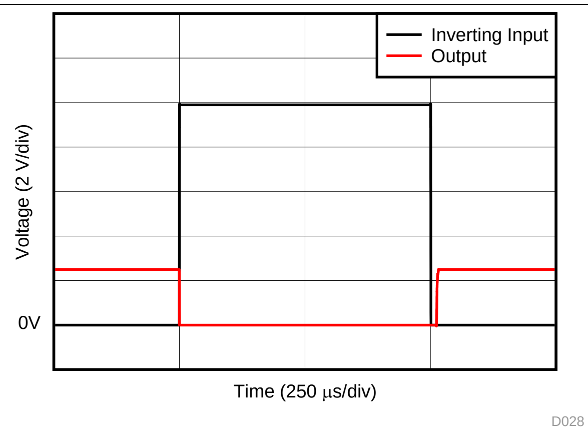


图 29. Inverting Differential Input Overload

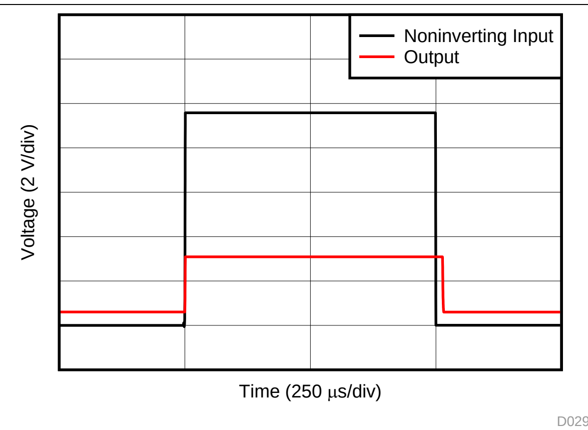


图 30. Noninverting Differential Input Overload

Typical Characteristics (接下页)

at T_A = 25°C, V_S = 5 V, V_{REF} = V_S / 2, and V_{IN+} = 12 V (unless otherwise noted)

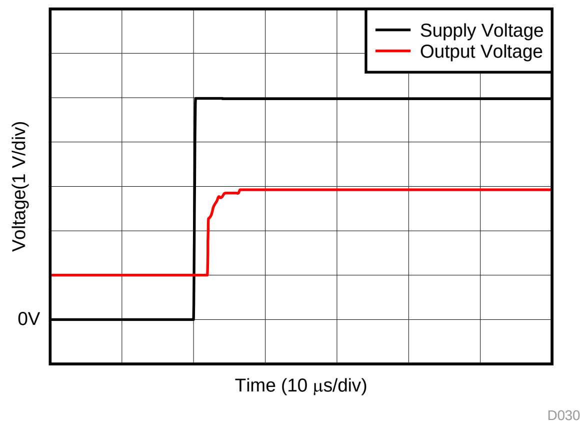


图 31. Start-Up Response

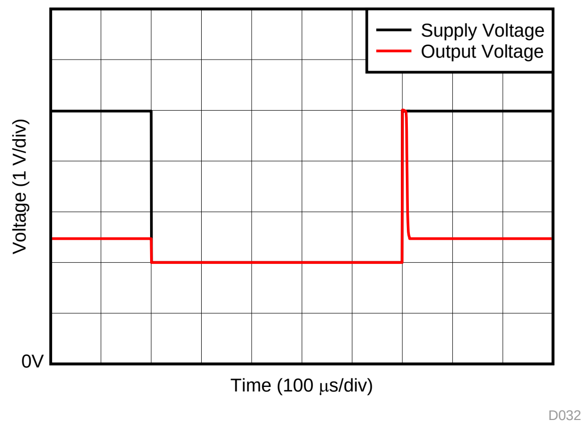


图 32. Brownout Recovery

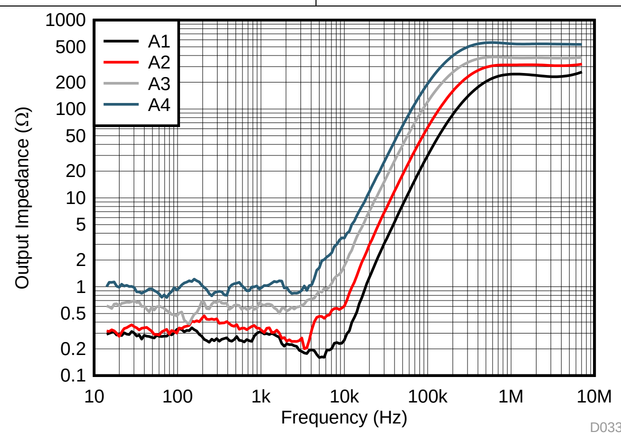


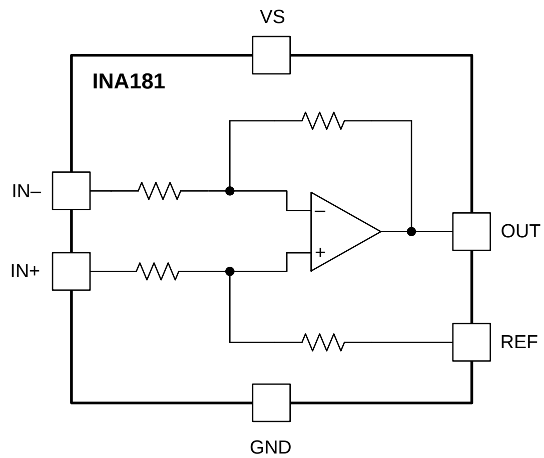
图 33. Output Impedance vs Frequency

8 Detailed Description

8.1 Overview

The INA181 is a 26-V, common-mode, current-sensing amplifier used in both low-side and high-side configurations. This specially-designed, current-sensing amplifier accurately measures voltages developed across current-sensing resistors on common-mode voltages that far exceed the supply voltage powering the device. Current can be measured on input voltage rails as high as 26 V, and the device can be powered from supply voltages as low as 2.7 V.

8.2 Functional Block Diagram



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8.3 Feature Description

8.3.1 High Bandwidth and Slew Rate

The INA181 supports small-signal bandwidths as high as 350 kHz, and large-signal slew rates of 2 V/µs. The ability to detect rapid changes in the sensed current, as well as the ability to quickly slew the output, make the INA181 a good choice for applications that require a quick response to input current changes. One application that requires high bandwidth and slew rate is low-side motor control, where the ability to follow rapid changing current in the motor allows for more accurate control over a wider operating range. Another application that requires higher bandwidth and slew rates is system fault detection, where the INA181 is used with an external comparator and a reference to quickly detect when the sensed current is out of range.

8.3.2 Bidirectional Current Monitoring

The INA181 senses current flow through a sense resistor in both directions. The bidirectional current-sensing capability is achieved by applying a voltage at the REF pin to offset the output voltage. A positive differential voltage sensed at the inputs results in an output voltage that is greater than the applied reference voltage; likewise, a negative differential voltage at the inputs results in output voltage that is less than the applied reference voltage. The output voltage of the current-sense amplifier is shown in 公式 1.

$$V_{OUT} = (I_{LOAD} \times R_{SENSE} \times GAIN) + V_{REF}$$

where

- I_{LOAD} is the load current to be monitored.
- R_{SENSE} is the current-sense resistor.
- GAIN is the gain option of the selected device.
- V_{REF} is the voltage applied to the REF pin. (1)

8.3.3 Wide Input Common-Mode Voltage Range

The INA181 supports input common-mode voltages from –0.2 V to +26 V. Because of the internal topology, the common-mode range is not restricted by the power-supply voltage (V_S) as long as V_S stays within the operational range of 2.7 V to 5.5 V. The ability to operate with common-mode voltages greater or less than V_S allow the INA181 to be used in high-side, as well as low-side, current-sensing applications, as shown in 图 34.

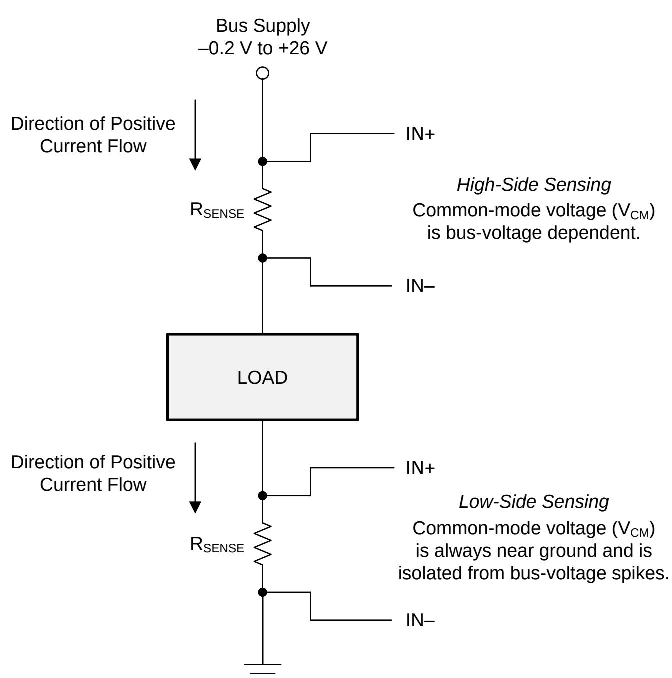


图 34. High-Side and Low-Side Sensing Connections

Feature Description (接下页)

8.3.4 Precise Low-Side Current Sensing

When used in low-side current sensing applications the offset voltage of the INA181 is less than 150 µV. The low offset performance of the INA181 has several benefits. First, the low offset allows the device to be used in applications that must measure current over a wide dynamic range. In this case, the low offset will improve the accuracy when the sensed currents are on the low end of the measurement range. Another advantage of low offset is the ability to sense lower voltage drop across the sense resistor accurately, thus allowing a lower-value shunt resistor. Lower-value shunt resistors reduce power loss in the current sense circuit, and help improve the power efficiency of the end application.

The gain error of the INA181 is specified to be within 1% of the actual value. As the sensed voltage becomes much larger than the offset voltage, this voltage becomes the dominant source of error in the current sense measurement.

8.3.5 Rail-to-Rail Output Swing

The INA181 allows linear current sensing operation with the output close to the supply rail and GND. The maximum specified output swing to the positive rail is 30 mV, and the maximum specified output swing to GND is only 5 mV. In order to compare the output swing of the INA181 to an equivalent operational amplifier (op amp), the inputs are overdriven to approximate the open-loop condition specified in op amp data sheets. The current-sense amplifier is a closed-loop system; therefore, the output swing to GND can be limited by the product of the offset voltage and amplifier gain during unidirectional operation (V_{REF} = 0 V).

For devices that have positive offset voltages, the swing to GND is limited by the larger of either the offset voltage multiplied by the gain or the swing to GND specified in the *Electrical Characteristics* table.

For example, in an application where the INA181A4 (gain = 200 V/V) is used for low-side current sensing and the device has an offset of 40 µV, the product of the device offset and gain results in a value of 8 mV, greater than the specified negative swing value. Therefore, the swing to GND for this example is 8 mV. If the same device has an offset of –40 µV, then the calculated zero differential signal is –8 mV. In this case, the offset helps overdrive the swing in the negative direction, and swing performance is consistent with the value specified in the *Electrical Characteristics* table.

The offset voltage is a function of the common-mode voltage as determined by the CMRR specification; therefore, the offset voltage increases when higher common-mode voltages are present. The increase in offset voltage limits how low the output voltage can go during a zero-current condition when operating at higher common-mode voltages with V_{REF} = 0 V . The typical limitation of the zero-current output voltage vs common-mode voltage for each gain option is shown in 图 35.

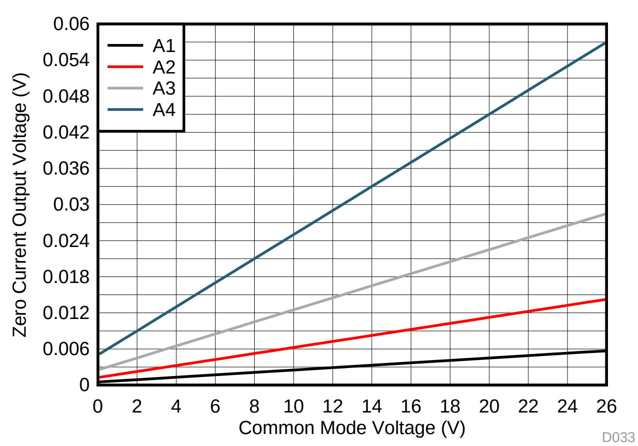


图 35. Zero-Current Output Voltage vs Common-Mode Voltage

8.4 Device Functional Modes

8.4.1 Normal Mode

The INA181 is in normal operation when the following conditions are met:

- The power supply voltage (V_S) is between 2.7 V and 5.5 V.
- The common-mode voltage (V_{CM}) is within the specified range of –0.2 V to +26 V.
- The maximum differential input signal times gain plus V_{REF} is less than V_S minus the output voltage swing to V_S.
- The minimum differential input signal times gain plus V_{REF} is greater than the swing to GND (see the *Rail-to-Rail Output Swing* section).

During normal operation, the device produces an output voltage that is the *gained-up* representation of the difference voltage from IN+ to IN– plus the reference voltage at V_{REF}.

8.4.2 Unidirectional Mode

The device can be configured to monitor current flowing in one direction (unidirectional) or in both directions (bidirectional) depending on how the REF pin is configured. The most common case is unidirectional where the output is set to ground when no current is flowing by connecting the REF pin to ground, as shown in 图 36. When the current flows from the bus supply to the load, the input signal across IN+ to IN– increases, and causes the output voltage at the OUT pin to increase.

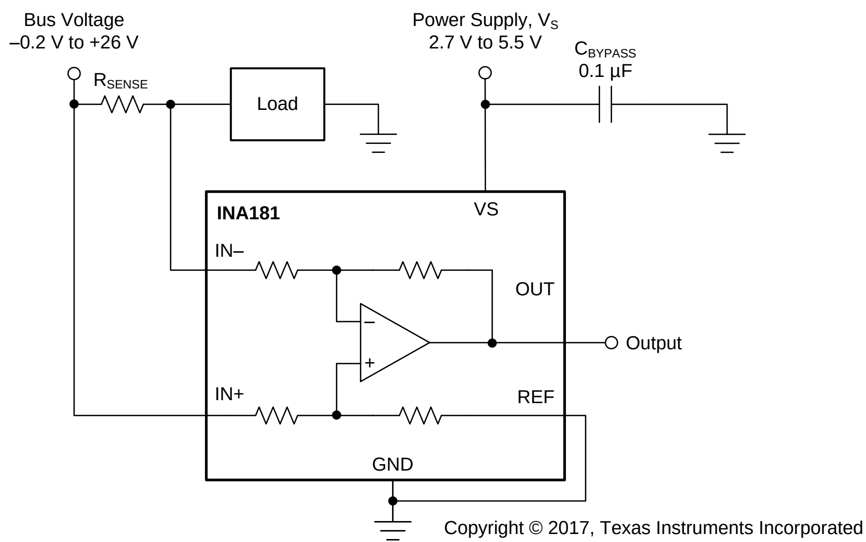


图 36. Unidirectional Application

The linear range of the output stage is limited by how close the output voltage can approach ground under zero input conditions. In unidirectional applications where measuring very low input currents is desirable, bias the REF pin to a convenient value above 50 mV to get the output into the linear range of the device. To limit common-mode rejection errors, buffer the reference voltage connected to the REF pin.

A less-frequently used output biasing method is to connect the REF pin to the power-supply voltage, V_S. This method results in the output voltage saturating at 200 mV less than the supply voltage when no differential input signal is present. This method is similar to the output saturated low condition with no input signal when the REF pin is connected to ground. The output voltage in this configuration only responds to negative currents that develop negative differential input voltage relative to the device IN– pin. Under these conditions, when the differential input signal increases negatively, the output voltage moves downward from the saturated supply voltage. The voltage applied to the REF pin must not exceed V_S.

Device Functional Modes (接下页)

8.4.3 Bidirectional Mode

The INA181 is a bidirectional, current-sense amplifier capable of measuring currents through a resistive shunt in two directions. This bidirectional monitoring is common in applications that include charging and discharging operations where the current flowing through the resistor can change directions.

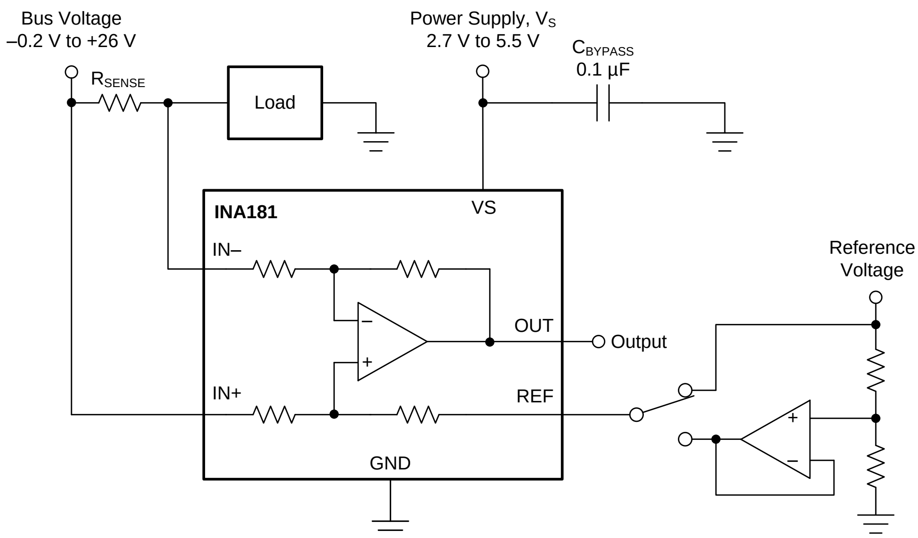


图 37. Bidirectional Application

The ability to measure this current flowing in both directions is enabled by applying a voltage to the REF pin, as shown in 图 37. The voltage applied to REF (V_{REF}) sets the output state that corresponds to the zero-input level state. The output then responds by increasing above V_{REF} for positive differential signals (relative to the IN– pin) and responds by decreasing below V_{REF} for negative differential signals. This reference voltage applied to the REF pin can be set anywhere between 0 V to V_S. For bidirectional applications, V_{REF} is typically set at mid-scale for equal signal range in both current directions. In some cases, however, V_{REF} is set at a voltage other than mid-scale when the bidirectional current and corresponding output signal do not need to be symmetrical.

8.4.4 Input Differential Overload

If the differential input voltage (V_{IN+} – $V_{IN–}$) times gain exceeds the voltage swing specification, the INA181 drives the output as close as possible to the positive supply or ground, and does not provide accurate measurement of the differential input voltage. If this input overload occurs during normal circuit operation, then reduce the value of the shunt resistor or use a lower-gain version with the chosen sense resistor to avoid this mode of operation. If a differential overload occurs in a fault event, then the output of the INA181 returns to the expected value approximately 20 µs after the fault condition is removed.

Device Functional Modes (接下页)

8.4.5 Shutdown Mode

Although the INA181 does not have a shutdown pin, the low power consumption of the device allows the output of a logic gate or transistor switch to power the INA181. This gate or switch turns on and off the INA181 power-supply quiescent current.

However, in current shunt monitoring applications, there is also a concern for how much current is drained from the shunt circuit in shutdown conditions. Evaluating this current drain involves considering the simplified schematic of the INA181 in shutdown mode, as shown in 图 38.

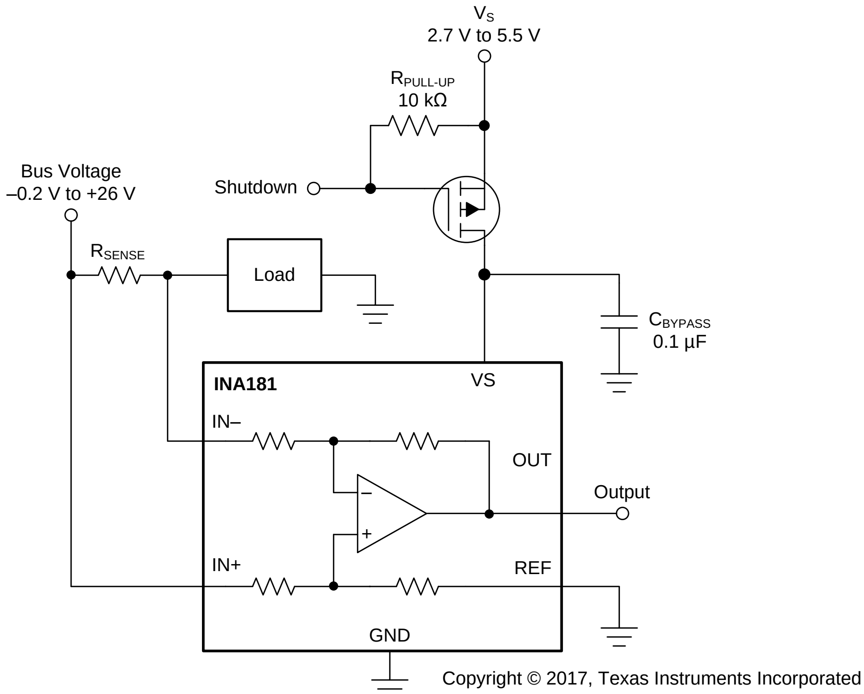


图 38. Basic Circuit to Shut Down the INA181 With a Grounded Reference

There is typically slightly more than 500 kΩ of impedance (from the combination of 500-kΩ feedback and input gain set resistors) from each input of the INA181 to the OUT pin and to the REF pin. The amount of current flowing through these pins depends on the voltage at the connection. For example, if the REF pin is grounded, the calculation of the effect of the 500 kΩ impedance from the shunt to ground is straightforward. However, if the reference is powered while the INA181 is in shutdown mode, instead of assuming 500 kΩ to ground, assume 500 kΩ to the reference voltage.

Regarding the 500-kΩ path to the output pin, the output stage of a disabled INA181 does constitute a good path to ground. Consequently, this current is directly proportional to a shunt common-mode voltage present across a 500-kΩ resistor.

As a final note, as long as the shunt common-mode voltage is greater than V_S when the device is powered up, there is an additional and well-matched 55-µA typical current that flows in each of the inputs. If less than V_S, the common-mode input currents are negligible, and the only current effects are the result of the 500-kΩ resistors.

9 Application and Implementation

注

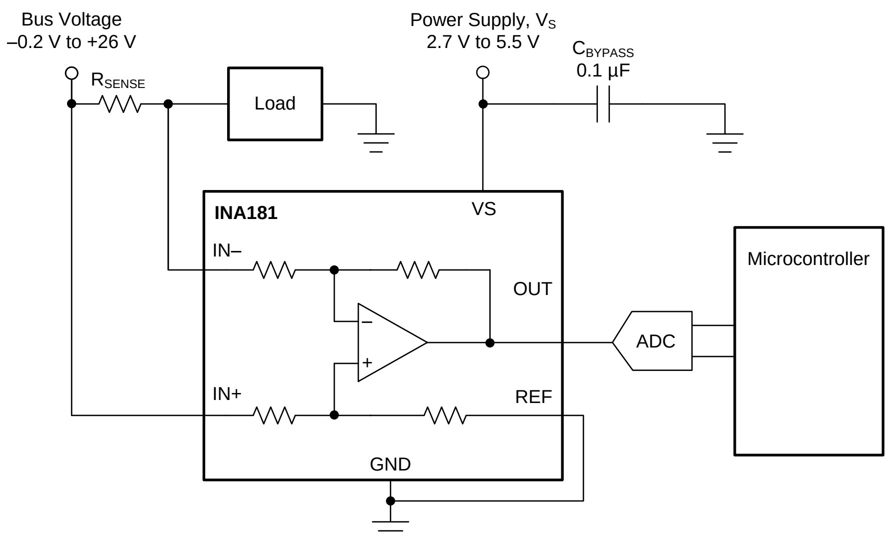
Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The INA181 amplifies the voltage developed across a current-sensing resistor as current flows through the resistor to the load or ground. The ability to drive the reference pin to adjust the functionality of the output signal offers multiple configurations, as discussed in previous sections.

9.1.1 Basic Connections

图 39 shows the basic connections of the INA181. Connect the input pins (IN+ and IN–) as closely as possible to the shunt resistor to minimize any resistance in series with the shunt resistor.



NOTE: To help eliminate ground offset errors between the device and the analog-to-digital converter (ADC), connect the REF pin to the ADC reference input and then to ground.

图 39. Basic Connections

A power-supply bypass capacitor of at least 0.1 µF is required for proper operation. Applications with noisy or high-impedance power supplies may require additional decoupling capacitors to reject power-supply noise. Connect bypass capacitors close to the device pins.

Application Information (接下页)

9.1.2 R_{SENSE} and Device Gain Selection

The accuracy of the INA181 is maximized by choosing the current-sense resistor to be as large as possible. A large sense resistor maximizes the differential input signal for a given amount of current flow and reduces the error contribution of the offset voltage. However, there are practical limits as to how large the current-sense resistor can be in a given application. The INA181 has a typical input bias currents of 75 µA for each input when operated at a 12-V common-mode voltage input. When large current-sense resistors are used, these bias currents cause increased offset error and reduced common-mode rejection. Therefore, using current-sense resistors larger than a few ohms is generally not recommended for applications that require current-monitoring accuracy. A second common restriction on the value of the current-sense resistor is the maximum allowable power dissipation that is budgeted for the resistor. 公式 2 gives the maximum value for the current sense resistor for a given power dissipation budget:

$$R_{SENSE} < \frac{PD_{MAX}}{I_{MAX}^{2}}$$

where:

- PD_{MAX} is the maximum allowable power dissipation in R_{SENSE}.
- I_{MAX} is the maximum current that will flow through R_{SENSE}. (2)

An additional limitation on the size of the current-sense resistor and device gain is due to the power-supply voltage, V_S, and device swing to rail limitations. In order to make sure that the current-sense signal is properly passed to the output, both positive and negative output swing limitations must be examined. 公式 3 provides the maximum values of R_{SENSE} and GAIN to keep the device from hitting the positive swing limitation.

$$I_{MAX} \times R_{SENSE} \times GAIN < Vs - V_{SP} - V_{REF}$$

where:

- I_{MAX} is the maximum current that will flow through R_{SENSE}.
- GAIN is the gain of the current sense-amplifier.
- V_S is the minimum supply voltage of the device.
- V_{SP} is the positive output swing as specified in the data sheet.
- V_{REF} is the externally applied voltage on the REF pin. (3)

To avoid positive output swing limitations when selecting the value of R_{SENSE}, there is always a trade-off between the value of the sense resistor and the gain of the device under consideration. If the sense resistor selected for the maximum power dissipation is too large, then it is possible to select a lower-gain device in order to avoid positive swing limitations.

The negative swing limitation places a limit on how small of a sense resistor can be used in a given application. 公式 4 provides the limit on the minimum size of the sense resistor.

$$I_{MIN} \times R_{SENSE} \times GAIN > V_{SN} - V_{REF}$$

where:

- I_{MIN} is the minimum current that will flow through R_{SENSE}.
- GAIN is the gain of the current sense amplifier.
- V_{SN} is the negative output swing of the device (see Rail-to-Rail Output Swing).
- V_{REF} is the externally applied voltage on the REF pin. (4)

In addition to adjusting the offset and gain, the voltage applied to the REF pin can be slightly increased to avoid negative swing limitations.

Application Information (接下页)

9.1.3 Signal Filtering

Provided that the INA181 output is connected to a high impedance input, the best location to filter is at the device output using a simple RC network from OUT to GND. Filtering at the output attenuates high-frequency disturbances in the common-mode voltage, differential input signal, and INA181 power-supply voltage. If filtering at the output is not possible, or filtering of only the differential input signal is required, it is possible to apply a filter at the input pins of the device. 图 40 provides an example of how a filter can be used on the input pins of the device.

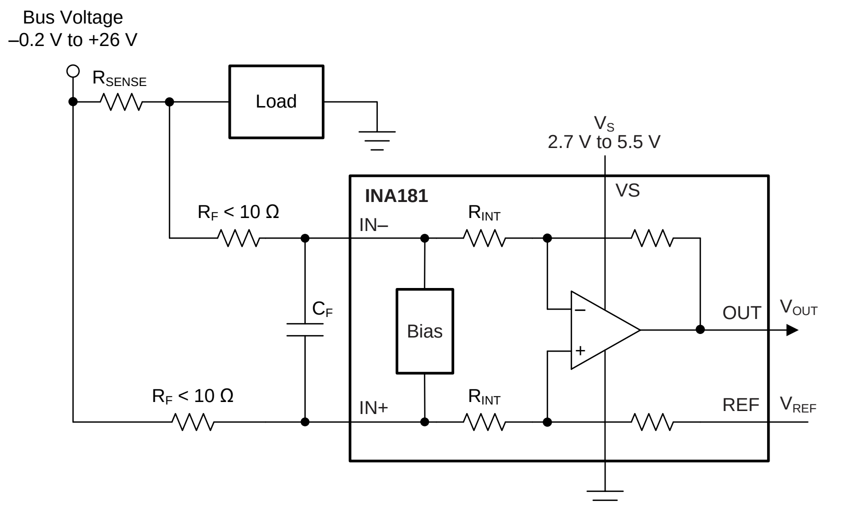


图 40. Filter at Input Pins

The addition of external series resistance creates an additional error in the measurement; therefore, the value of these series resistors must be kept to 10 Ω (or less, if possible) to reduce impact to accuracy. The internal bias network shown in 图 40 present at the input pins creates a mismatch in input bias currents when a differential voltage is applied between the input pins. If additional external series filter resistors are added to the circuit, the mismatch in bias currents results in a mismatch of voltage drops across the filter resistors. This mismatch creates a differential error voltage that subtracts from the voltage developed across the shunt resistor. This error results in a voltage at the device input pins that is different than the voltage developed across the shunt resistor. Without the additional series resistance, the mismatch in input bias currents has little effect on device operation. The amount of error these external filter resistors add to the measurement can be calculated using 公式 6, where the gain error factor is calculated using 公式 5.

The amount of variance in the differential voltage present at the device input relative to the voltage developed at the shunt resistor is based both on the external series resistance (R_F) value as well as internal input resistor R_{INT}, as shown in 图 40. The reduction of the shunt voltage reaching the device input pins appears as a gain error when comparing the output voltage relative to the voltage across the shunt resistor. A factor can be calculated to determine the amount of gain error that is introduced by the addition of external series resistance. Calculate the expected deviation from the shunt voltage to what is measured at the device input pins is given using 公式 5:

$$\text{Gain Error Factor} = \frac{1250 \times R_{INT}}{(1250 \times R_F) + (1250 \times R_{INT}) + (R_F \times R_{INT})}$$

where:

- R_{INT} is the internal input resistor.
- R_F is the external series resistance. (5)

Application Information (接下页)

With the adjustment factor from 公式 5, including the device internal input resistance, this factor varies with each gain version, as shown in 表 1. Each individual device gain error factor is shown in 表 2.

表 1. Input Resistance

PRODUCT	GAIN	R_{INT} (kΩ)
INA181A1	20	25
INA181A2	50	10
INA181A3	100	5
INA181A4	200	2.5

表 2. Device Gain Error Factor

PRODUCT	SIMPLIFIED GAIN ERROR FACTOR
INA181A1	$\frac{25000}{(21 \times R_F) + 25000}$
INA181A2	$\frac{10000}{(9 \times R_F) + 10000}$
INA181A3	$\frac{1000}{R_F + 1000}$
INA181A4	$\frac{2500}{(3 \times R_F) + 2500}$

The gain error that can be expected from the addition of the external series resistors can then be calculated based on 公式 6:

$$\text{Gain Error (\%)} = 100 - (100 \times \text{Gain Error Factor}) \quad (6)$$

For example, using an INA180A2 and the corresponding gain error equation from 表 2, a series resistance of 10 Ω results in a gain error factor of 0.991. The corresponding gain error is then calculated using 公式 6, resulting in an additional gain error of approximately 0.89% solely because of the external 10-Ω series resistors.

9.2 Typical Application

One application for the INA181 is to monitor bidirectional currents. Bidirectional currents are present in systems that have to monitor currents in both directions; common examples are monitoring the charging and discharging of batteries and bidirectional current monitoring in motor control. The device configuration for bidirectional current monitoring is shown in 图 41. Applying stable REF pin voltage closer to the middle of device supply voltage allows both positive- and negative-current monitoring, as shown in this configuration. Configure the INA181 to monitor unidirectional currents by grounding the REF pin.

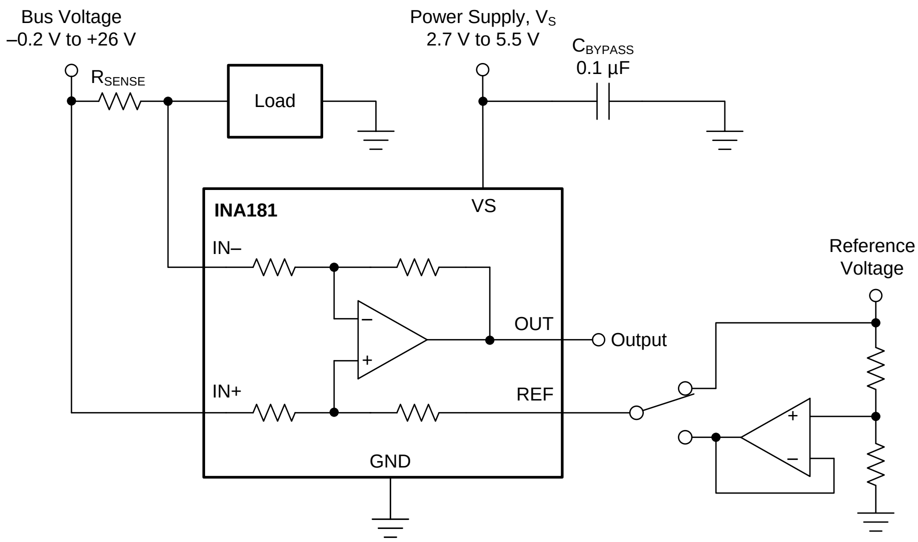


图 41. Bidirectional Application

9.2.1 Design Requirements

The design requirements for the circuit shown in 图 41, are listed in 表 3

表 3. Design Parameters

DESIGN PARAMETER	EXAMPLE VALUE
Power-supply voltage, V_S	5 V
Bus supply rail, V_{CM}	12 V
Mode of operation	Bidirectional
R_{SENSE} power loss	< 450 mW
Maximum sense current, I_{MAX}	±20 A
Accuracy	Less than 3.5% at maximum current, T_J = 25°C
Small-signal bandwidth	> 100 kHz

9.2.2 Detailed Design Procedure

The maximum value of the current sense resistor is calculated based on the maximum power loss requirement. By applying 公式 2, the maximum value of the current-sense resistor is calculated to be 1.125 mΩ. This is the maximum value for sense resistor R_{SENSE}; therefore, select R_{SENSE} to be 1 mΩ because it is the closest standard resistor value that meets the power-loss requirement.

The next step is to select the appropriate gain and reduce R_{SENSE}, if needed, to keep the output signal swing within the V_S range. The design requirements call for bidirectional current monitoring; therefore, a voltage between 0 and V_S must be applied to the REF pin. The bidirectional currents monitored are symmetric around 0 (that is, ±20 A); therefore, the ideal voltage to apply to V_{REF} is V_S / 2 or 2.5 V. If the positive current is greater than the negative current, using a lower voltage on V_{REF} has the benefit of maximizing the output swing for the given range of expected currents. Using 公式 3, and given that I_{MAX} = 20 A , R_{SENSE} = 1 mΩ, and V_{REF} = 2.5 V, the maximum current-sense gain calculated to avoid the positive swing-to-rail limitations on the output is 122.5. Likewise, using 公式 4 for the negative-swing limitation results in a maximum gain of 124.75. Selecting the gain-of-100 device maximizes the output range while staying within the output swing range. If the maximum calculated gains are slightly less than 100, the value of the current-sense resistor can be reduced to keep the output from hitting the output-swing limitations.

To calculate the accuracy at peak current, the two factors that must be determined are the gain error and the offset error. The gain error of the INA181 is specified to be a maximum of 1%. The error due to the offset is constant, and is specified to be 500 µV (maximum) for the conditions where V_{CM} = 12 V and V_S = 5 V. Using 公式 7, the percentage error contribution of the offset voltage is calculated to be 2.5%, with total offset error = 500 µV, R_{SENSE} = 1 mΩ, and I_{SENSE} = 20 A.

$$\text{Total Offset Error (\%)} = \frac{\text{Total Offset Error (V)}}{I_{SENSE} \times R_{SENSE}} \times 100\% \quad (7)$$

One method of calculating the total error is to add the gain error to the percentage contribution of the offset error. However, in this case, the gain error and the offset error do not have an influence or correlation to each other. A more statistically accurate method of calculating the total error is to use the RMS sum of the errors, as shown in 公式 8.

$$\text{Total Error (\%)} = \sqrt{\text{Total Gain Error (\%)}^2 + \text{Total Offset Error (\%)}^2} \quad (8)$$

After applying 公式 8, the total current sense error at maximum current is calculated to be 2.7%, and that is less than the design example requirement of 3.5%.

The gain-of-100 device also has a bandwidth of 150 kHz that meets the small-signal bandwidth requirement of 100 kHz. If higher bandwidth is required, lower-gain devices can be used at the expense of either reduced output voltage range or an increased value of R_{SENSE}.

9.2.3 Application Curve

An example output response of a bidirectional configuration is shown in 图 42. With the REF pin connected to a reference voltage (2.5 V in this case), the output voltage is biased upwards by this reference level. The output rises above the reference voltage for positive differential input signals, and falls below the reference voltage for negative differential input signals.

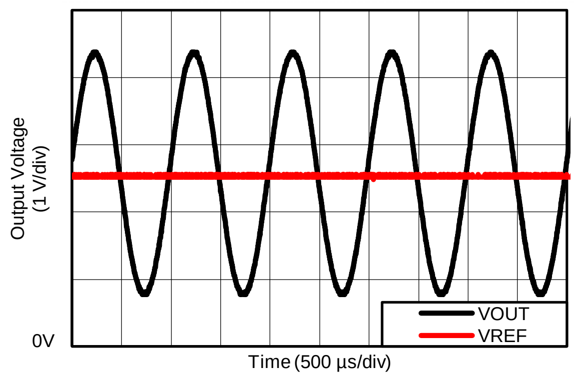


图 42. Bidirectional Application Output Response

10 Power Supply Recommendations

The input circuitry of the INA181 accurately measures beyond the power-supply voltage, V_S. For example, V_S can be 5 V, whereas the bus supply voltage at IN+ and IN– can be as high as 26 V. However, the output voltage range of the OUT pin is limited by the voltages on the VS pin. The INA181 also withstands the full differential input signal range up to 26 V at the IN+ and IN– input pins, regardless of whether or not the device has power applied at the VS pin.

10.1 Common-Mode Transients Greater Than 26 V

With a small amount of additional circuitry, the INA181 can be used in circuits subject to transients higher than 26 V, such as automotive applications. Use only Zener diodes or Zener-type transient absorbers (sometimes referred to as *transzorbs*)—any other type of transient absorber has an unacceptable time delay. Start by adding a pair of resistors as a working impedance for the Zener diode; see 图 43. Keep these resistors as small as possible; most often, around 10 Ω. Larger values can be used with an effect on gain that is discussed in the *Signal Filtering* section. This circuit limits only short-term transients; therefore, many applications are satisfied with a 10-Ω resistor along with conventional Zener diodes of the lowest acceptable power rating. This combination uses the least amount of board space. These diodes can be found in packages as small as SOT-523 or SOD-523.

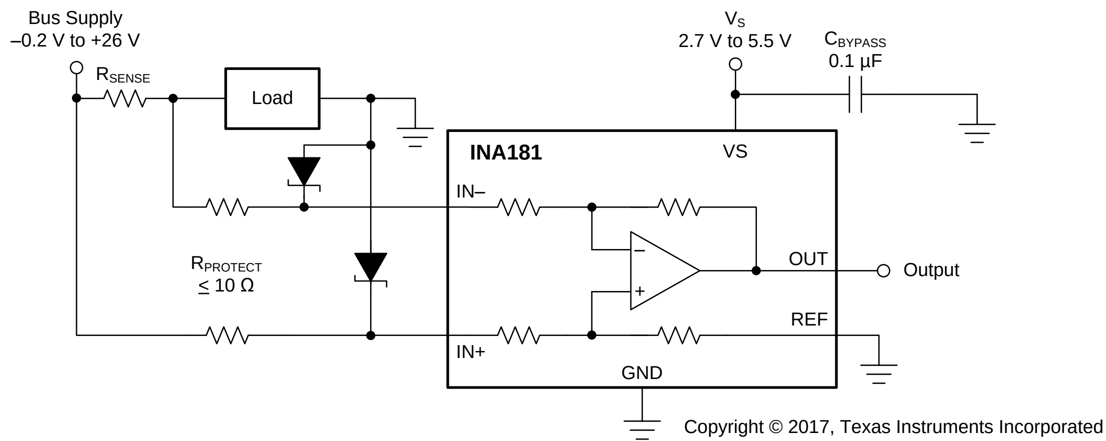


图 43. Transient Protection Using Dual Zener Diodes

In the event that low-power Zener diodes do not have sufficient transient absorption capability, a higher-power transzorb must be used. The most package-efficient solution involves using a single transzorb and back-to-back diodes between the device inputs, as shown in 图 44. The most space-efficient solutions are dual, series-connected diodes in a single SOT-523 or SOD-523 package. In either of the examples shown in 图 43 and 图 44, the total board area required by the INA181 with all protective components is less than that of an SO-8 package, and only slightly greater than that of an MSOP-8 package.

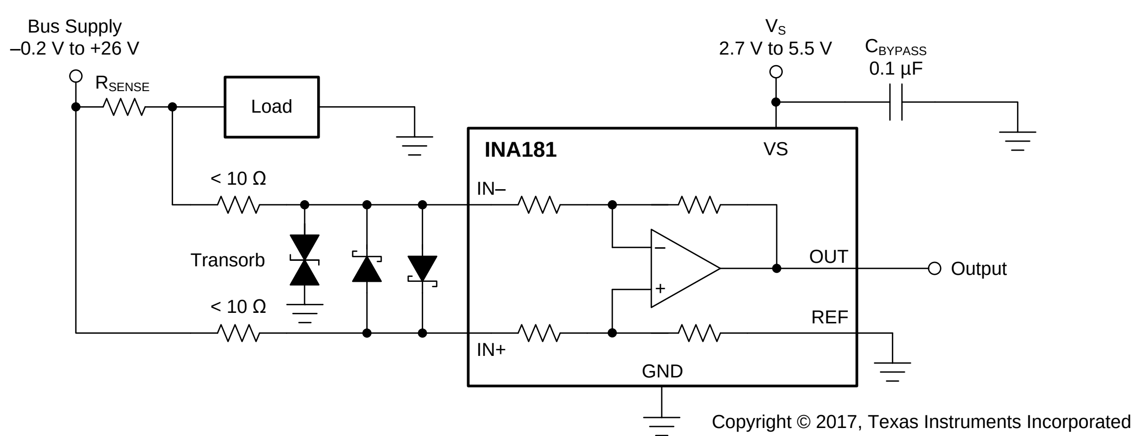


图 44. Transient Protection Using a Single Transzorb and Input Clamps

11 Layout

11.1 Layout Guidelines

- Connect the input pins to the sensing resistor using a Kelvin or 4-wire connection. This connection technique makes sure that only the current-sensing resistor impedance is detected between the input pins. Poor routing of the current-sensing resistor commonly results in additional resistance present between the input pins. Given the very low ohmic value of the current resistor, any additional high-current carrying impedance can cause significant measurement errors.
- Place the power-supply bypass capacitor as close as possible to the device power supply and ground pins. The recommended value of this bypass capacitor is 0.1 µF. Additional decoupling capacitance can be added to compensate for noisy or high-impedance power supplies.

11.2 Layout Example

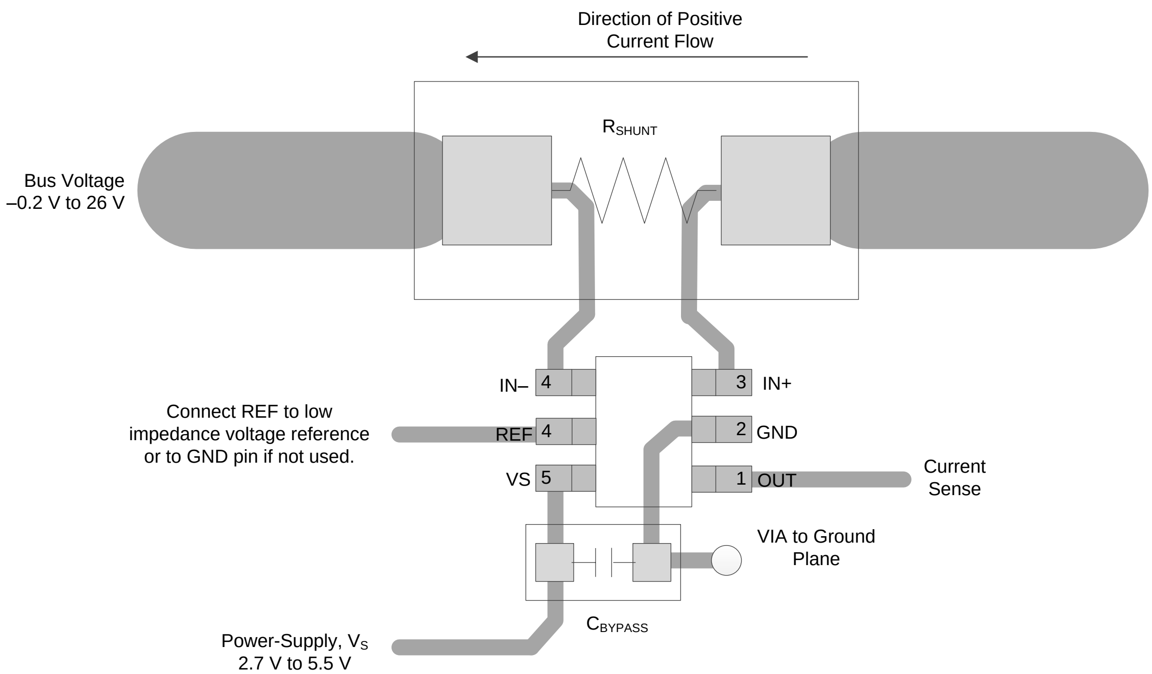


图 45. Recommended Layout

12 器件和文档支持

12.1 文档支持

12.1.1 相关文档

相关文档如下：

- 《INA180-181EVM 用户指南》(SBOU183)

12.2 接收文档更新通知

如需接收文档更新通知，请访问 www.ti.com.cn 网站上的器件产品文件夹。点击右上角的*提醒我* (Alert me) 注册后，即可每周定期收到已更改的产品信息。有关更改的详细信息，请查阅已修订文档中包含的修订历史记录。

12.3 社区资源

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community ***TI's Engineer-to-Engineer (E2E) Community.*** Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support ***TI's Design Support*** Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.4 商标

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12.5 静电放电警告

ESD 可能会损坏该集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理措施和安装程序，可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级，大至整个器件故障。 精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

12.6 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

13 机械、封装和可订购信息

以下页中包括机械、封装和可订购信息。这些信息是针对指定器件可提供的最新数据。这些数据会在无通知且不对本文档进行修订的情况下发生改变。欲获得该数据表的浏览器版本，请查阅左侧的导航栏。

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
INA181A1IDBVR	ACTIVE	SOT-23	DBV	6	3000	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	18JD	Samples
INA181A1IDBVT	ACTIVE	SOT-23	DBV	6	250	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	18JD	Samples
INA181A2IDBVR	ACTIVE	SOT-23	DBV	6	3000	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	1AED	Samples
INA181A2IDBVT	ACTIVE	SOT-23	DBV	6	250	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	1AED	Samples
INA181A3IDBVR	ACTIVE	SOT-23	DBV	6	3000	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	1AFD	Samples
INA181A3IDBVT	ACTIVE	SOT-23	DBV	6	250	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	1AFD	Samples
INA181A4IDBVR	ACTIVE	SOT-23	DBV	6	3000	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	1AGD	Samples
INA181A4IDBVT	ACTIVE	SOT-23	DBV	6	250	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	1AGD	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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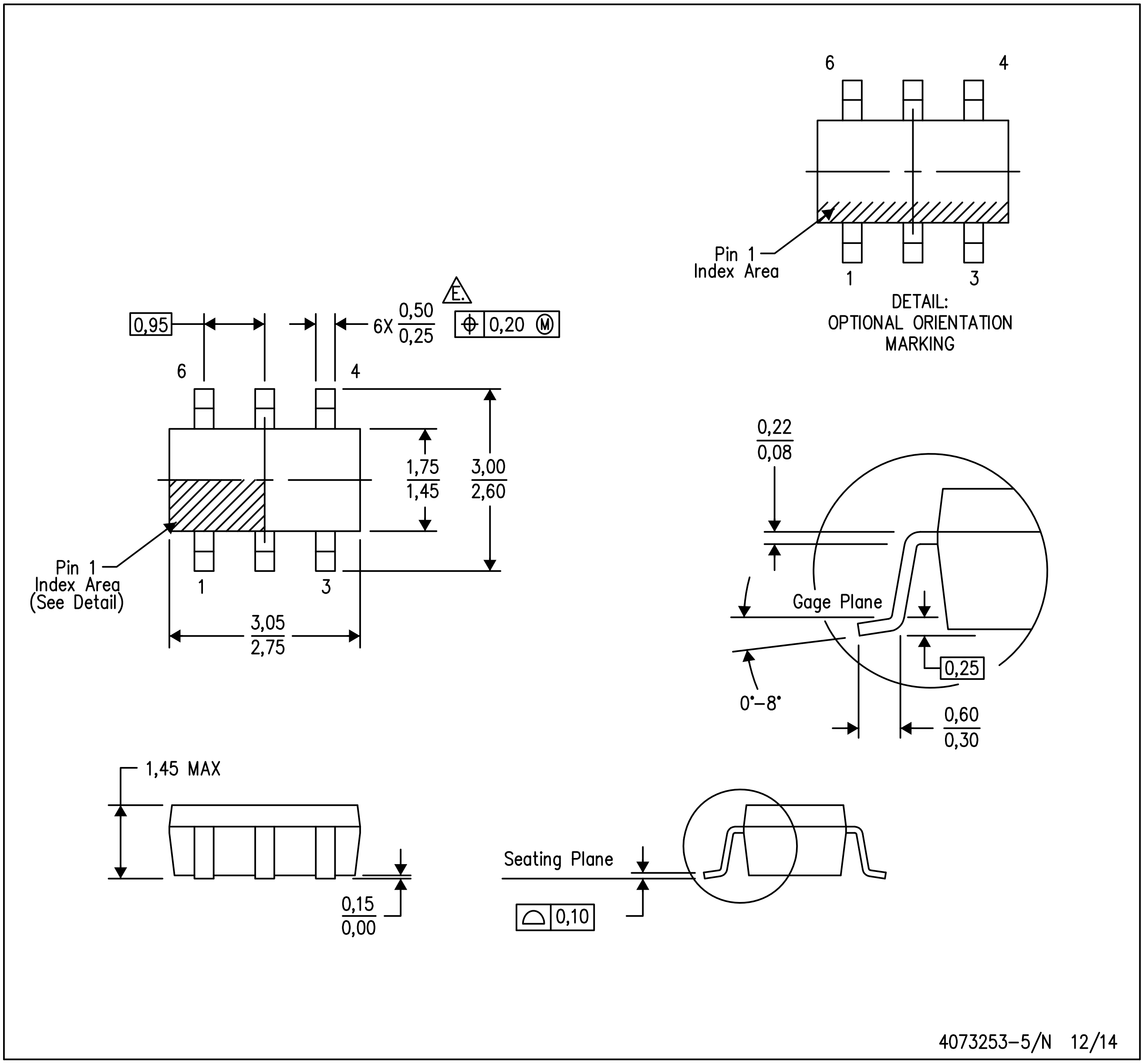
DBV (R-PDSO-G6) PLASTIC SMALL-OUTLINE PACKAGE



NOTES:
- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
- D. Leads 1,2,3 may be wider than leads 4,5,6 for package orientation.
- E. Falls within JEDEC MO-178 Variation AB, except minimum lead width.

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